

Title (en)
ETCHING SOLUTION AND METHOD

Title (de)
ÄTZLÖSUNG UND VERFAHREN

Title (fr)
SOLUTION DECAPANTE ET PROCEDE

Publication
EP 1256126 A1 20021113 (EN)

Application
EP 01905084 A 20010126

Priority
• US 0102569 W 20010126
• US 49786400 A 20000204

Abstract (en)
[origin: WO0157921A1] An etching solution of Hydrogen Fluoride (HF), carboxylic acid and water having a high etch selectivity for silicon oxide relative to metal, polysilicon and nitride. The etching solution is created by injecting anhydrous HF into a carboxylic acid having a precisely controlled minimal amount of water. The etching solution is useful in the fabrication of Micro Electro-Mechanical System (MEMS) devices, as well as the fabrication of MEMS devices in combination with integrated electronics on the same chip.

IPC 1-7
H01L 21/311; C09K 13/08

IPC 8 full level
B81C 1/00 (2006.01); **C09K 13/08** (2006.01); **H01L 21/308** (2006.01); **H01L 21/311** (2006.01)

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C09K 13/08 (2013.01 - EP KR); **H01L 21/31111** (2013.01 - EP KR)

Citation (search report)
See references of WO 0157921A1

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